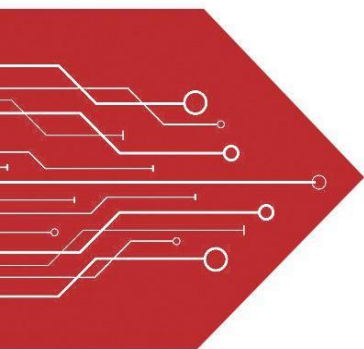


MSKSEMI

SEMICONDUCTOR



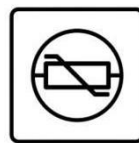
ESD



TVS



TSS



MOV



GDT

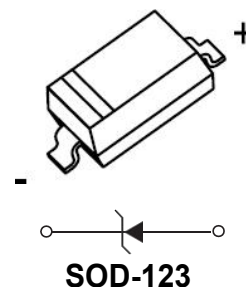


PLED

Product data sheet

FEATURES

- Planar Die Construction
- Ultra-Small Surface Mount Package
- General purpose, Medium Current
- Ideally Suited for Automated Assembly Processes



Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

Parameters	Symbol	Value	Unit
Power Dissipation	Pd	500 ¹⁾	mW
Forward Voltage @IF=10mA	Vf	0.9 ²⁾	V
Storage temperature range	Ts	-65-+150	°C
Thermal resistance junction to ambient air Warmewiderstand Sperrschicht – umgebende Luft	RthA	400	K/W ¹⁾

1) Device mounted on ceramic PCB: 7.6mm x 9.4mm x 0.87mm with pad areas 25mm²

2) Short duration test pulse used to minimize self-heating effect

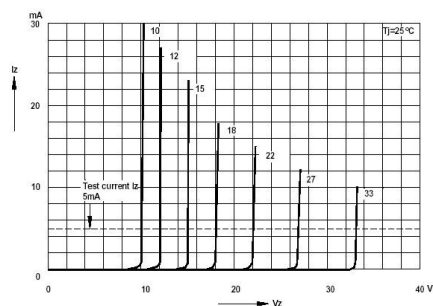
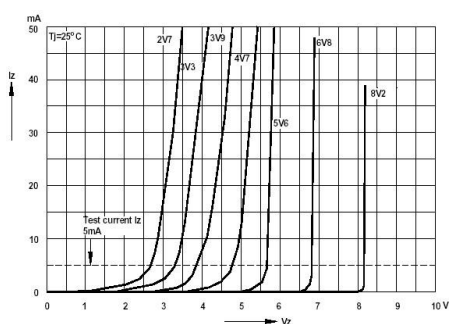
3) f=1KHz

Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified).

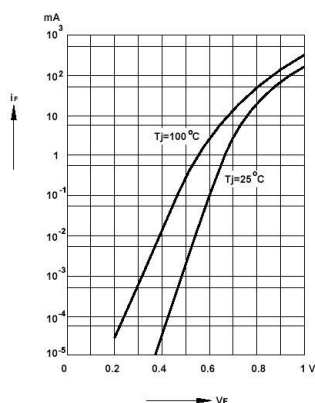
Device	Marking	Zener Voltage Range				Maximum Zener Impedance ³⁾			Maximum Reverse Current		Typical Temperature coefficient @ IZTC=mV/°C		Test Current IZTC
		Vz@Izt			Izt	Zzt @Izt	Zzk @Izk	Izk	IR	VR	Min	Max	mA
		Nom(V)	Min(V)	Max(V)	mA	Ω		mA	uA	V			
BZT52C2V0	WY	2.0	1.80	2.15	5	150	600	1.0	100	1.0	-3.5	0	5
BZT52C2V4	WX	2.4	2.2	2.6	5	100	600	1.0	50	1.0	-3.5	0	5
BZT52C2V7	W1	2.7	2.5	2.9	5	100	600	1.0	20	1.0	-3.5	0	5
BZT52C3V0	W2	3.0	2.8	3.2	5	95	600	1.0	10	1.0	-3.5	0	5
BZT52C3V3	W3	3.3	3.1	3.5	5	95	600	1.0	5	1.0	-3.5	0	5
BZT52C3V6	W4	3.6	3.4	3.8	5	90	600	1.0	5	1.0	-3.5	0	5
BZT52C3V9	W5	3.9	3.7	4.1	5	90	600	1.0	3	1.0	-3.5	0	5
BZT52C4V3	W6	4.3	4.0	4.6	5	90	600	1.0	3	1.0	-3.5	0	5
BZT52C4V7	W7	4.7	4.4	5.0	5	80	500	1.0	3	2.0	-3.5	0.2	5
BZT52C5V1	W8	5.1	4.8	5.4	5	60	480	1.0	2	2.0	-2.7	1.2	5
BZT52C5V6	W9	5.6	5.2	6.0	5	40	400	1.0	1	2.0	-2.0	2.5	5
BZT52C6V2	WA	6.2	5.8	6.6	5	10	150	1.0	3	4.0	0.4	3.7	5
BZT52C6V8	WB	6.8	6.4	7.2	5	15	80	1.0	2	4.0	1.2	4.5	5
BZT52C7V5	WC	7.5	7.0	7.9	5	15	80	1.0	1	5.0	2.5	5.3	5
BZT52C8V2	WD	8.2	7.7	8.7	5	15	80	1.0	0.7	5.0	3.2	6.2	5
BZT52C9V1	WE	9.1	8.5	9.6	5	15	100	1.0	0.5	6.0	3.8	7.0	5
BZT52C10	WF	10	9.4	10.6	5	20	150	1.0	0.2	7.0	4.5	8.0	5

Device	Marking	Zener Voltage Range				Maximum Zener Impedance			Maximum Reverse Current		Typical Temperature coefficient @ IZTC=mV/°C		Test Current IZTC
		Vz@Izt			Izt	Zzt @Izt	Zzk @Izk	Izk	IR	VR	Min	Max	
		Nom(V)	Min(V)	Max(V)	mA	Ω		mA	μA	V			
BZT52C11	WG	11	10.4	11.6	5	20	150	1.0	0.1	8.0	5.4	9.0	5
BZT52C12	WH	12	11.4	12.7	5	25	150	1.0	0.1	8.0	6.0	10.0	5
BZT52C13	WI	13	12.4	14.1	5	30	170	1.0	0.1	8.0	7.0	11.0	5
BZT52C15	WJ	15	13.8	15.6	5	30	200	1.0	0.1	10.5	9.2	13.0	5
BZT52C16	WK	16	15.3	17.1	5	40	200	1.0	0.1	11.2	10.4	14.0	5
BZT52C18	WL	18	16.8	19.1	5	45	225	1.0	0.1	12.6	12.4	16.0	5
BZT52C20	WM	20	18.8	21.2	5	55	225	1.0	0.1	14.0	14.4	18.0	5
BZT52C22	WN	22	20.8	23.3	5	55	250	1.0	0.1	15.4	16.4	20.0	5
BZT52C24	WO	24	22.8	25.6	5	70	250	1.0	0.1	16.8	18.4	22.0	5
BZT52C27	WP	27	25.1	28.9	2	80	300	0.5	0.1	18.9	21.4	25.3	2
BZT52C30	WQ	30	28.0	32.0	2	80	300	0.5	0.1	21.0	24.4	29.4	2
BZT52C33	WR	33	31.0	35.0	2	80	325	0.5	0.1	23.1	27.4	33.4	2
BZT52C36	WS	36	34.0	38.0	2	90	350	0.5	0.1	25.2	30.4	37.4	2
BZT52C39	WT	39	37.0	41.0	2	130	350	0.5	0.1	27.3	33.4	41.2	2
BZT52C43	WU	43	40.0	46.0	2	100	700	1.0	0.1	32.0	10.0	12.0	5
BZT52C47	WV	47	44.0	50.0	2	100	750	1.0	0.1	35.0	10.0	12.0	5
BZT52C51	WW	51	48.0	54.0	2	125	750	1.0	0.1	38.0	10.0	12.0	5
BZT52C56	XW	56	52.0	60.0	2	135	700	1.0	0.1	39.0	10.0	12.0	5
BZT52C62	6E	62	58.0	66.0	2	200	1000	1.0	0.2	47.0	10.0	12.0	5
BZT52C68	6F	68	64.0	72.0	2	250	1000	1.0	0.2	52.0	10.0	12.0	5
BZT52C75	6H	75	70.0	79.0	2	300	1000	1.0	0.2	57	10.0	12.0	5

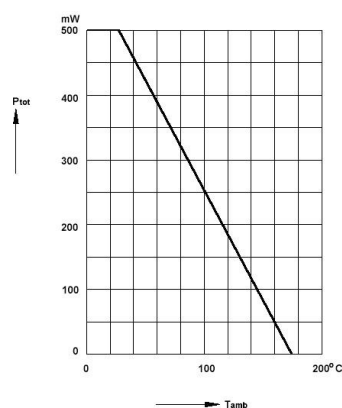
Breakdown characteristics at Tj=constant (pulsed)



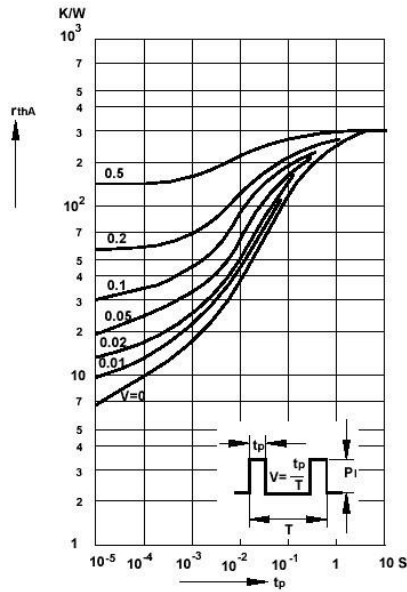
Forward characteristics



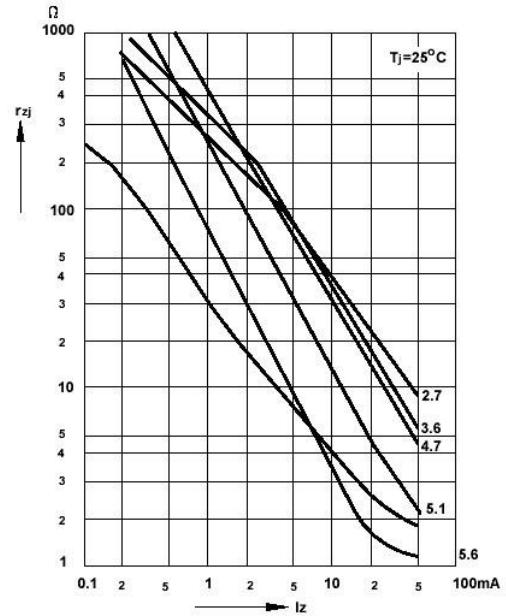
Admissible power dissipation versus ambient temperature



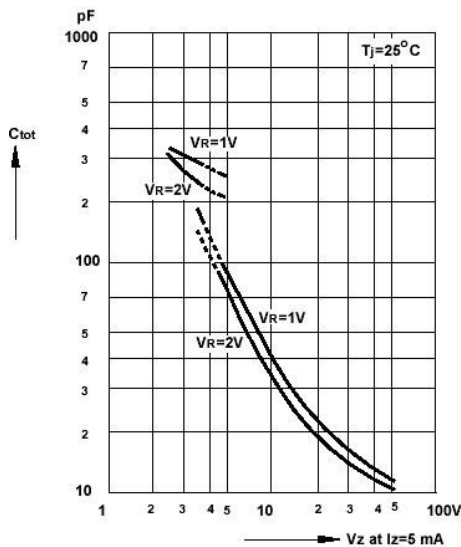
Pulse thermal resistance versus pulse duration



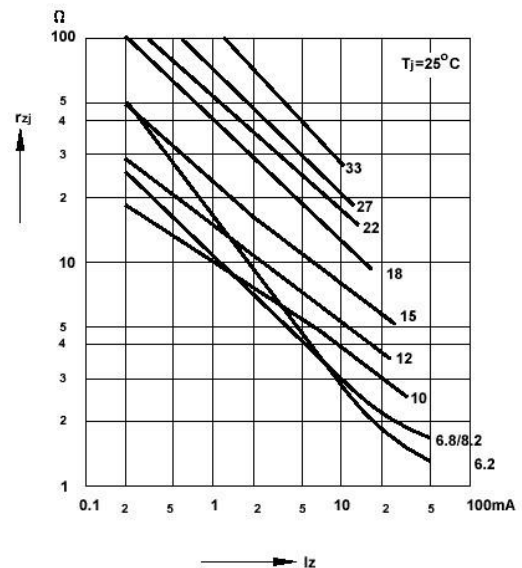
Dynamic resistance versus Zener current



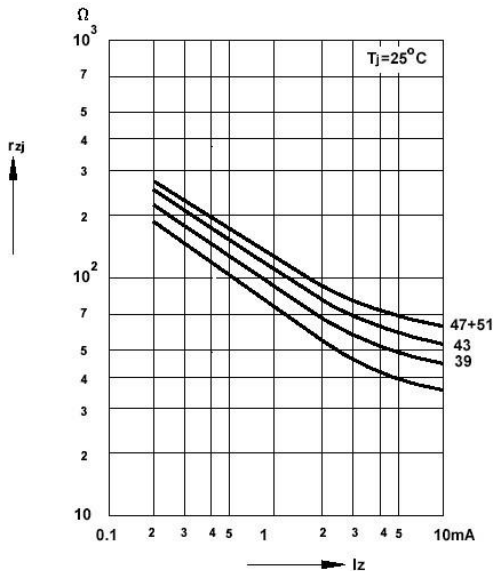
Capacitance versus Zener voltage



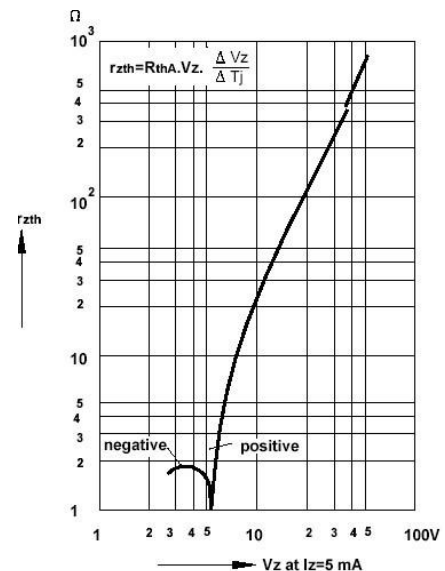
Dynamic resistance versus Zener current



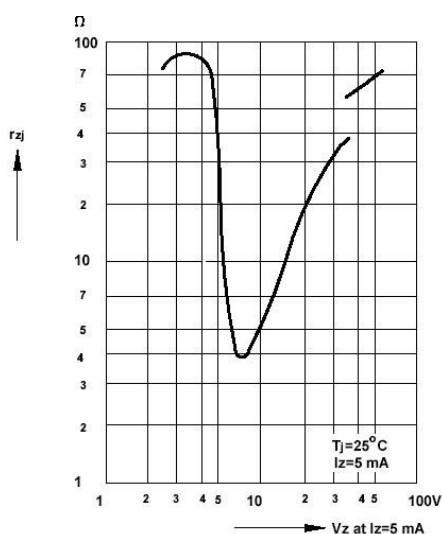
Dynamic resistance versus Zener current



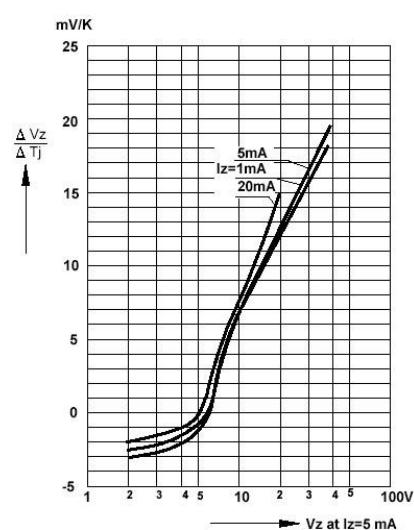
Thermal differential resistance versus Zener voltage



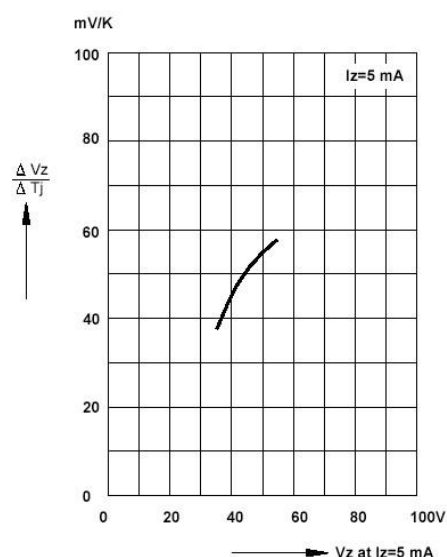
Dynamic resistance versus Zener voltage



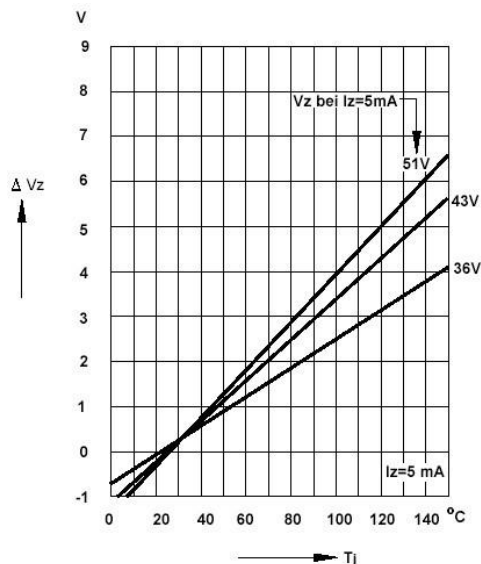
Temperature dependence of Zener voltage versus Zener voltage



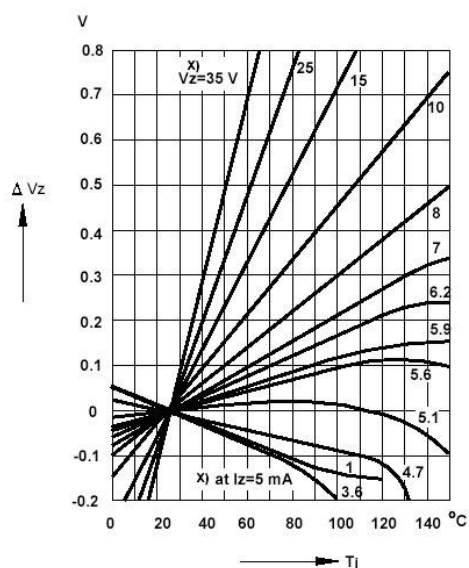
Temperature dependence of Zener voltage versus Zener voltage



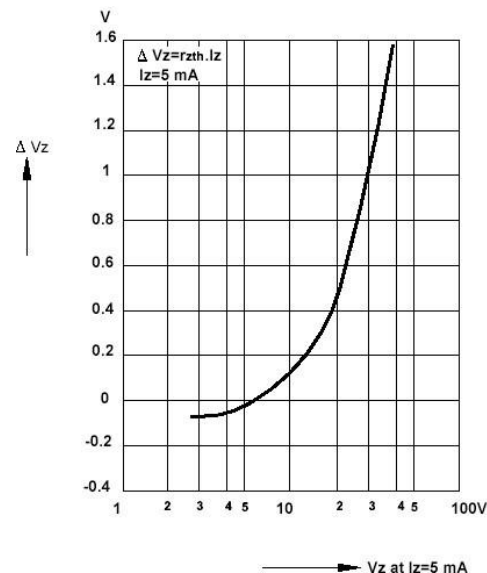
Change of Zener voltage versus junction temperature



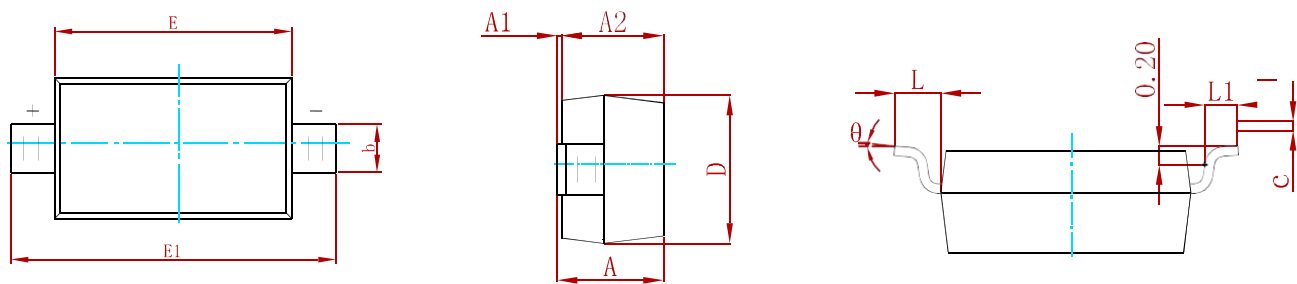
Change of Zener voltage versus junction temperature



Change of Zener voltage from turn-on up to the point of thermal equilibrium versus Zener voltage

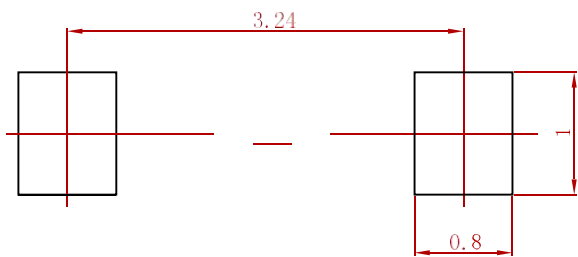


PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.450	0.650	0.018	0.026
c	0.080	0.150	0.003	0.006
D	1.500	1.700	0.059	0.067
E	2.600	2.800	0.102	0.110
E1	3.550	3.850	0.140	0.152
L	0.500 REF		0.020 REF	
L1	0.250	0.450	0.010	0.018
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
BZT52CXX	SOD-123	3000

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